

## P-Channel 20 V (D-S) MOSFET

### DESCRIPTION

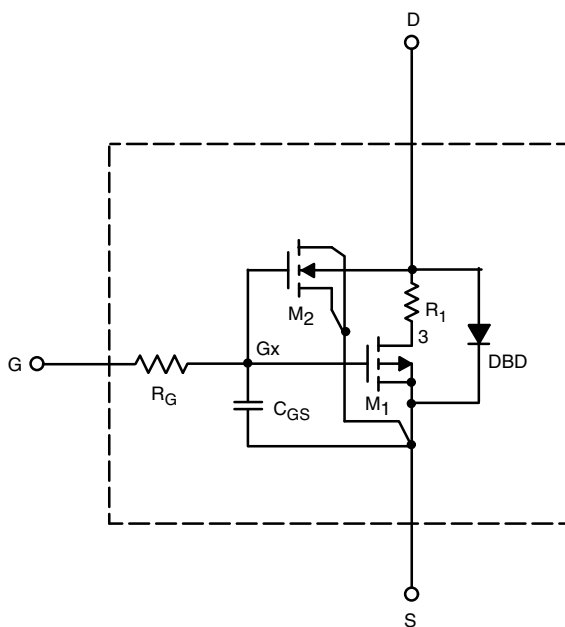
The attached SPICE model describes the typical electrical characteristics of the p-channel vertical DMOS. The subcircuit model is extracted and optimized over the - 55 °C to 125 °C temperature ranges under the pulsed 0 V to 5 V gate drive. The saturated output impedance is best fit at the gate bias near the threshold voltage.

A novel gate-to-drain feedback capacitance network is used to model the gate charge characteristics while avoiding convergence difficulties of the switched  $C_{gd}$  model. All model parameter values are optimized to provide a best fit to the measured electrical data and are not intended as an exact physical interpretation of the device.

### CHARACTERISTICS

- P-Channel Vertical DMOS
- Macro Model (Subcircuit Model)
- Level 3 MOS
- Apply for both Linear and Switching Application
- Accurate over the - 55 °C to + 125 °C Temperature Range
- Model the Gate Charge

### SUBCIRCUIT MODEL SCHEMATIC



### Note

- This document is intended as a SPICE modeling guideline and does not constitute a commercial product datasheet. Designers should refer to the appropriate datasheet of the same number for guaranteed specification limits.



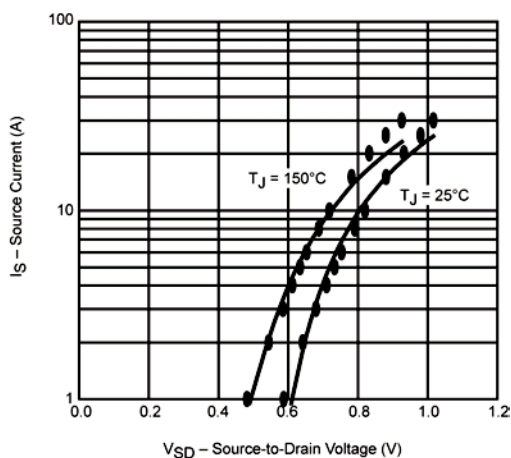
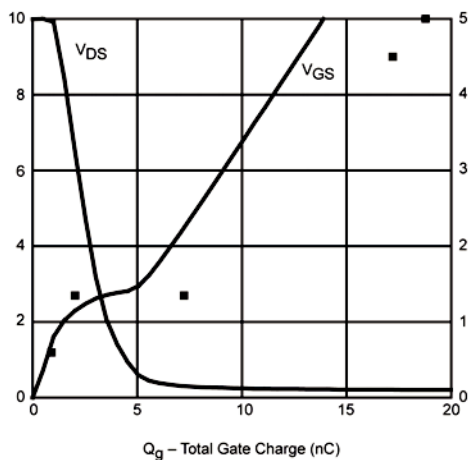
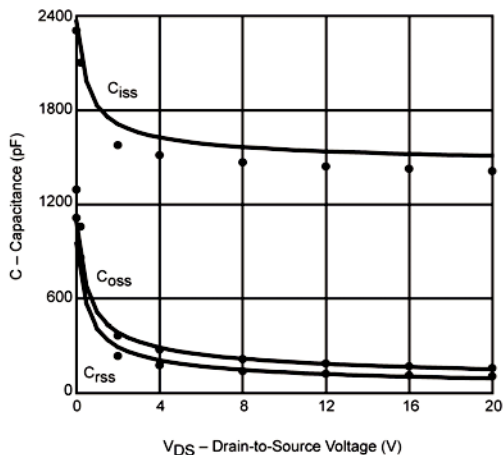
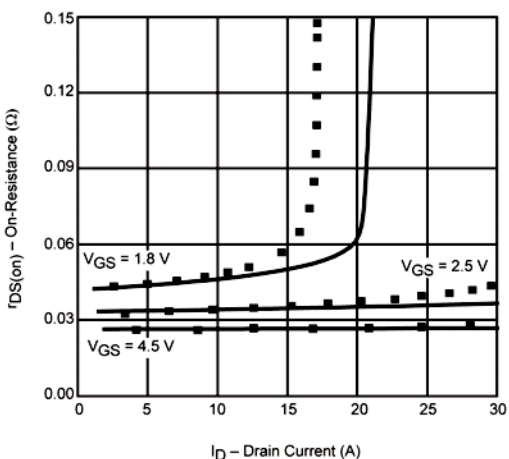
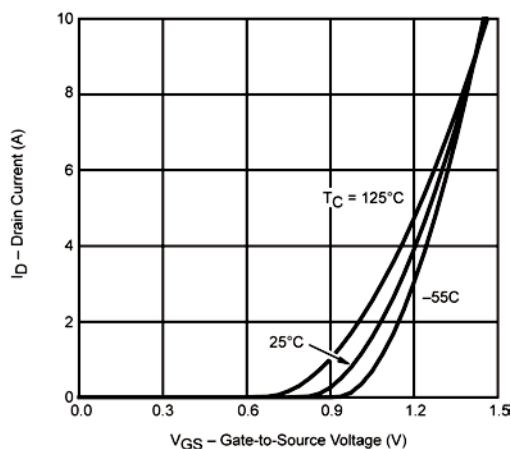
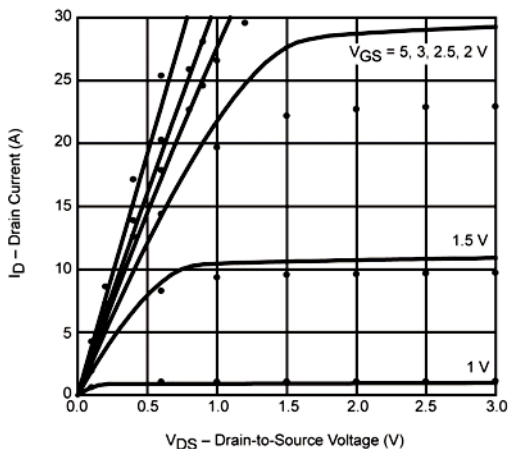
SPECIFICATIONS ( $T_J = 25\text{ }^{\circ}\text{C}$ , unless otherwise noted)					
PARAMETER	SYMBOL	TEST CONDITIONS	SIMULATED DATA	MEASURED DATA	UNIT
<b>Static</b>					
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}$ , $I_D = -250\text{ }\mu\text{A}$	0.66	-	V
On-State Drain Current <sup>a</sup>	$I_{D(on)}$	$V_{DS} \leq -5\text{ V}$ , $V_{GS} = -4.5\text{ V}$	165	-	A
Drain-Source On-State Resistance <sup>a</sup>	$R_{DS(on)}$	$V_{GS} = -4.5\text{ V}$ , $I_D = -5.9\text{ A}$	0.027	0.025	$\Omega$
		$V_{GS} = -2.5\text{ V}$ , $I_D = -5.1\text{ A}$	0.033	0.032	
		$V_{GS} = -1.8\text{ V}$ , $I_D = -2\text{ A}$	0.043	0.042	
Forward Transconductance <sup>a</sup>	$g_{fs}$	$V_{DS} = -10\text{ V}$ , $I_D = -5.9\text{ A}$	46	20	S
Diode Forward Voltage	$V_{SD}$	$I_S = -7\text{ A}$	-0.94	-0.80	V
<b>Dynamic<sup>b</sup></b>					
Input Capacitance	$C_{iss}$	$V_{DS} = -10\text{ V}$ , $V_{GS} = 0\text{ V}$ , $f = 1\text{ MHz}$	1550	1500	pF
Output Capacitance	$C_{oss}$		203	210	
Reverse Transfer Capacitance	$C_{rss}$		135	150	
Total Gate Charge	$Q_g$	$V_{DS} = -10\text{ V}$ , $V_{GS} = -5\text{ V}$ , $I_D = -8.8\text{ A}$	14	19	nC
		$V_{DS} = -10\text{ V}$ , $V_{GS} = -4.5\text{ V}$ , $I_D = -8.8\text{ A}$	13	17.5	
Gate-Source Charge	$Q_{gs}$		2.1	2.1	
Gate-Drain Charge	$Q_{gd}$		5.2	5.2	

**Notes**

- a. Pulse test; pulse width  $\leq 300\text{ }\mu\text{s}$ , duty cycle  $\leq 2\%$ .  
b. Guaranteed by design, not subject to production testing.



## COMPARISON OF MODEL WITH MEASURED DATA ( $T_J = 25^\circ\text{C}$ , unless otherwise noted)



### Note

- Dots and squares represent measured data.